

BLC6G10-200; BLC6G10LS-200

UHF power LDMOS transistor

Rev. 01 — 19 April 2006

Objective data sheet

1. Product profile

1.1 General description

200 W LDMOS power transistor for base station applications at frequencies from 800 MHz to 1000 MHz.

Table 1: Typical performance

Typical RF performance at $T_{case} = 25\text{ °C}$ in a class-AB production test circuit.

Mode of operation	f (MHz)	V _{DS} (V)	P _{L(AV)} (W)	G _p (dB)	η _D (%)	ACPR (dBc)
2-carrier W-CDMA	869 to 894	28	40	20	27	-39 ^[1]

[1] Test signal: 3GPP; test model 1; 64 DPCH; PAR = 7.5 dB at 0.01 % probability on CCDF per carrier; carrier spacing 5 MHz.

CAUTION



This device is sensitive to ElectroStatic Discharge (ESD). Therefore care should be taken during transport and handling.

1.2 Features

- Typical 2-carrier W-CDMA performance at frequencies of 869 MHz and 894 MHz, a supply voltage of 28 V and an I_{DQ} of 1400 mA:
 - ◆ Average output power = 40 W
 - ◆ Power gain = 20 dB
 - ◆ Efficiency = 27 %
 - ◆ ACPR = -39 dBc
- Easy power control
- Integrated ESD protection
- Excellent ruggedness
- High efficiency
- Excellent thermal stability
- Designed for broadband operation (800 MHz to 1000 MHz)
- Internally matched for ease of use

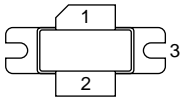
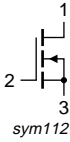
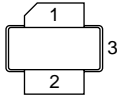
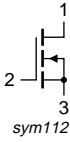
1.3 Applications

- RF power amplifiers for GSM, GSM EDGE, W-CDMA and CDMA base stations and multi carrier applications in the 800 MHz to 1000 MHz frequency range.

PHILIPS

2. Pinning information

Table 2: Pinning

Pin	Description	Simplified outline	Symbol
BLC6G10-200 (SOT895-1)			
1	drain		 sym112
2	gate		
3	source		
BLC6G10LS-200 (SOT896-1)			
1	drain		 sym112
2	gate		
3	source		

[1] Connected to flange

3. Ordering information

Table 3: Ordering information

Type number	Package		
	Name	Description	Version
BLC6G10-200	-	plastic flanged cavity package; 2 mounting slots; 2 leads	SOT895-1
BLC6G10LS-200	-	plastic earless flanged cavity package; 2 leads	SOT896-1

4. Limiting values

Table 4: Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DS}	drain-source voltage		-	65	V
V_{GS}	gate-source voltage		-0.5	+13	V
I_D	drain current		-	<td>	A
T_{stg}	storage temperature		-65	+150	°C
T_j	junction temperature		-	200	°C

5. Thermal characteristics

Table 5: Thermal characteristics

Symbol	Parameter	Conditions	Type	Min	Typ	Max	Unit
$R_{th(j-case)}$	thermal resistance from junction to case	$T_{case} = 80\text{ °C};$ $P_L = 40\text{ W}$	BLC6G10-200	<td>	<td>	<td>	K/W
			BLC6G10LS-200	<td>	0.43	0.52	K/W

6. Characteristics

Table 6: Characteristics

$T_j = 25\text{ °C}$ unless otherwise specified

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$V_{(BR)DSS}$	drain-source breakdown voltage	$V_{GS} = 0\text{ V}; I_D = 0.5\text{ mA}$	65	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	$V_{DS} = 10\text{ V}; I_D = 150\text{ mA}$	<td>	2	<td>	V
V_{GSq}	gate-source quiescent voltage	$V_{DS} = 28\text{ V}; I_D = 950\text{ mA}$	<td>	<td>	<td>	V
I_{DSS}	drain leakage current	$V_{GS} = 0\text{ V}; V_{DS} = 28\text{ V}$	-	-	5	μA
I_{DSX}	drain cut-off current	$V_{GS} = V_{GS(th)} + 3.75\text{ V};$ $V_{DS} = 10\text{ V}$	40	45	-	A
I_{GSS}	gate leakage current	$V_{GS} = 13\text{ V}; V_{DS} = 0\text{ V}$	-	-	450	nA
g_{fs}	forward transconductance	$V_{DS} = 10\text{ V}; I_D = 7.5\text{ A}$	-	<td>	-	S
$R_{DS(on)}$	drain-source on-state resistance	$V_{GS} = V_{GS(th)} + 3.75\text{ V};$ $I_D = 5.25\text{ A}$	-	<td>	-	Ω
C_{rs}	feedback capacitance	$V_{GS} = 0\text{ V}; V_{DS} = 28\text{ V};$ $f = 1\text{ MHz}$	-	<td>	-	pF

7. Application information

Table 7: Application information

Mode of operation: 2-carrier W-CDMA; PAR 7.5 dB at 0.01 % probability on CCDF; 3GPP test model 1; 1-64 PDPCH; $f_1 = 871.5\text{ MHz}; f_2 = 876.5\text{ MHz}; f_3 = 886.5\text{ MHz}; f_4 = 891.5\text{ MHz};$ RF performance at $V_{DS} = 28\text{ V}; I_{Dq} = 1400\text{ mA}; T_{case} = 25\text{ °C};$ unless otherwise specified; in a class-AB production test circuit

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$P_{L(AV)}$	average output power		-	40	-	W
G_p	power gain	$P_{L(AV)} = 40\text{ W}$	18.5	20	21.5	dB
IRL	input return loss	$P_{L(AV)} = 40\text{ W}$	-	-6.5	-4.5	dB
η_D	drain efficiency	$P_{L(AV)} = 40\text{ W}$	25	27	-	%
ACPR	adjacent channel power ratio	$P_{L(AV)} = 40\text{ W}$	-	-39	-36	dBc

7.1 Ruggedness in class-AB operation

The BLC6G10-200 and BLC6G10LS-200 are capable of withstanding a load mismatch corresponding to VSWR = <td> through all phases under the following conditions: $V_{DS} = 28\text{ V}; I_{Dq} = 1400\text{ mA}; P_L = \text{<td>}; f = 894\text{ MHz}.$

8. Package outline

Plastic flanged cavity package; 2 mounting slots; 2 leads

SOT895-1

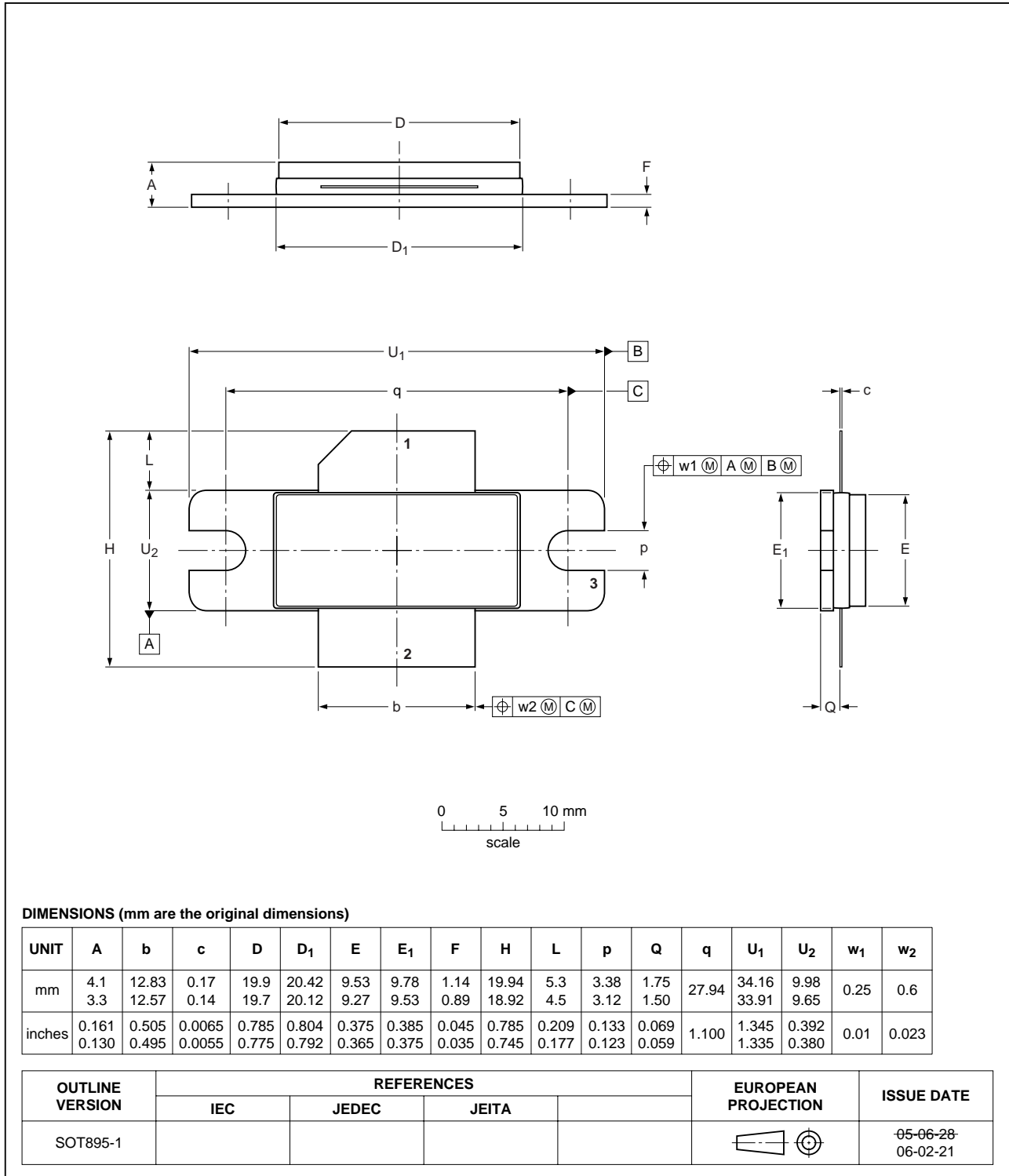


Fig 1. Package outline SOT895-1

Plastic earless flanged cavity package; 2 leads

SOT896-1

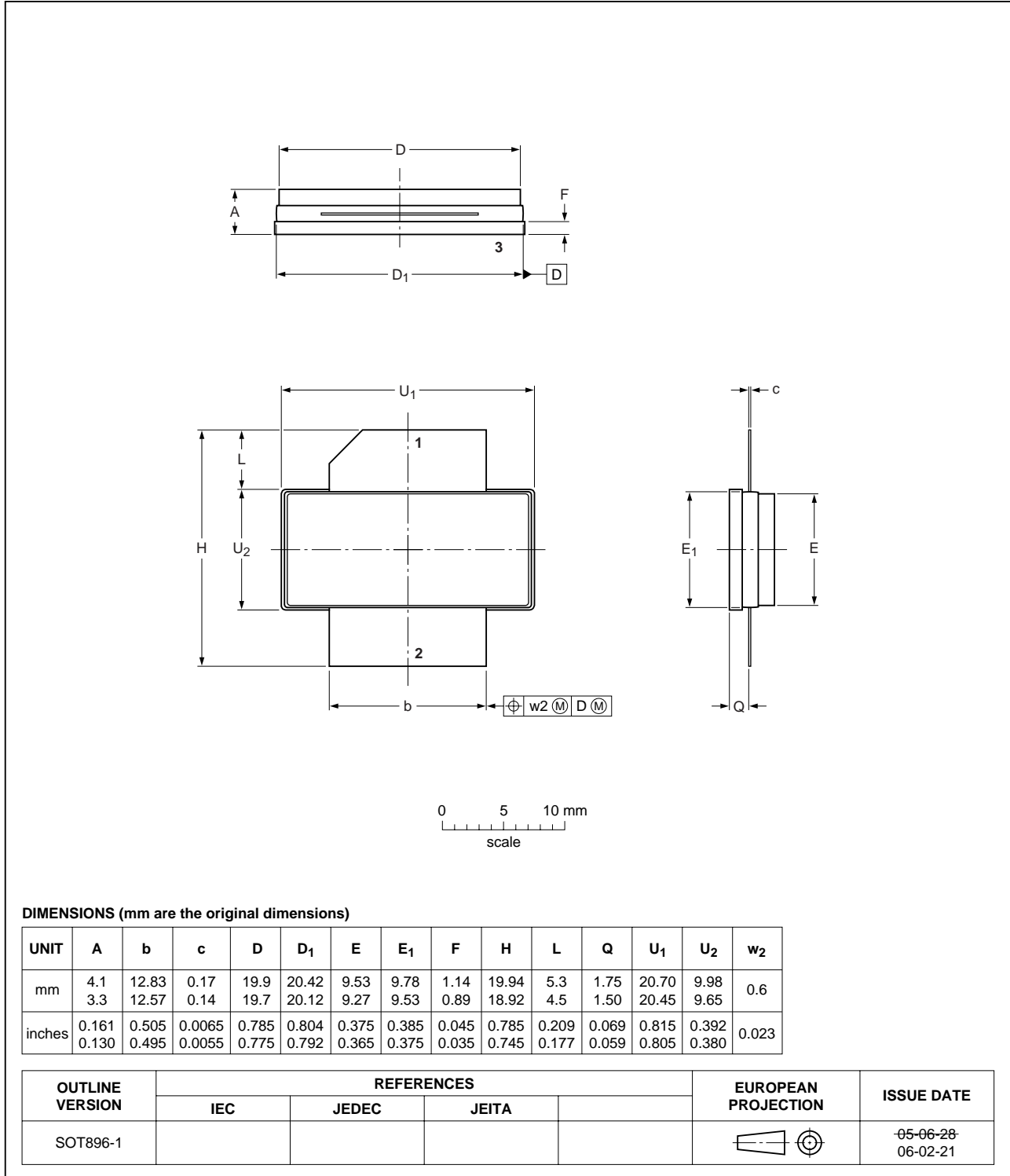


Fig 2. Package outline SOT896-1

9. Abbreviations

Table 8: Abbreviations

Acronym	Description
3GPP	Third Generation Partnership Project
CCDF	Complementary Cumulative Distribution Function
CDMA	Code Division Multiple Access
CW	Continuous Wave
DPCH	Dedicated Physical CHannel
EDGE	Enhanced Data rates for GSM Evolution
GSM	Global System for Mobile communications
LDMOS	Laterally Diffused Metal Oxide Semiconductor
PAR	Peak-to-Average power Ratio
PDPCH	transmission Power of the Dedicated Physical CHannel
RF	Radio Frequency
VSWR	Voltage Standing Wave Ratio
W-CDMA	Wideband Code Division Multiple Access

10. Revision history

Table 9: Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
BLC6G10-200_6G10LS-200_1	20060419	Objective data sheet	-	-

11. Legal information

11.1 Data sheet status

Document status ^{[1][2]}	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

[3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL <http://www.semiconductors.philips.com>.

11.2 Definitions

Draft — The document is a draft version only. The content is still under internal review and subject to formal approval, which may result in modifications or additions. Philips Semiconductors does not give any representations or warranties as to the accuracy or completeness of information included herein and shall have no liability for the consequences of use of such information.

Short data sheet — A short data sheet is an extract from a full data sheet with the same product type number(s) and title. A short data sheet is intended for quick reference only and should not be relied upon to contain detailed and full information. For detailed and full information see the relevant full data sheet, which is available on request via the local Philips Semiconductors sales office. In case of any inconsistency or conflict with the short data sheet, the full data sheet shall prevail.

11.3 Disclaimers

General — Information in this document is believed to be accurate and reliable. However, Philips Semiconductors does not give any representations or warranties, expressed or implied, as to the accuracy or completeness of such information and shall have no liability for the consequences of use of such information.

Right to make changes — Philips Semiconductors reserves the right to make changes to information published in this document, including without limitation specifications and product descriptions, at any time and without notice. This document supersedes and replaces all information supplied prior to the publication hereof.

Suitability for use — Philips Semiconductors products are not designed, authorized or warranted to be suitable for use in medical, military, aircraft, space or life support equipment, nor in applications where failure or

malfunction of a Philips Semiconductors product can reasonably be expected to result in personal injury, death or severe property or environmental damage. Philips Semiconductors accepts no liability for inclusion and/or use of Philips Semiconductors products in such equipment or applications and therefore such inclusion and/or use is for the customer's own risk.

Applications — Applications that are described herein for any of these products are for illustrative purposes only. Philips Semiconductors makes no representation or warranty that such applications will be suitable for the specified use without further testing or modification.

Limiting values — Stress above one or more limiting values (as defined in the Absolute Maximum Ratings System of IEC 60134) may cause permanent damage to the device. Limiting values are stress ratings only and operation of the device at these or any other conditions above those given in the Characteristics sections of this document is not implied. Exposure to limiting values for extended periods may affect device reliability.

Terms and conditions of sale — Philips Semiconductors products are sold subject to the general terms and conditions of commercial sale, as published at <http://www.semiconductors.philips.com/profile/terms>, including those pertaining to warranty, intellectual property rights infringement and limitation of liability, unless explicitly otherwise agreed to in writing by Philips Semiconductors. In case of any inconsistency or conflict between information in this document and such terms and conditions, the latter will prevail.

No offer to sell or license — Nothing in this document may be interpreted or construed as an offer to sell products that is open for acceptance or the grant, conveyance or implication of any license under any copyrights, patents or other industrial or intellectual property rights.

11.4 Trademarks

Notice: All referenced brands, product names, service names and trademarks are the property of their respective owners.

12. Contact information

For additional information, please visit: <http://www.semiconductors.philips.com>

For sales office addresses, send an email to: sales.addresses@www.semiconductors.philips.com

13. Contents

1	Product profile	1
1.1	General description	1
1.2	Features	1
1.3	Applications	1
2	Pinning information	2
3	Ordering information	2
4	Limiting values	2
5	Thermal characteristics	3
6	Characteristics	3
7	Application information	3
7.1	Ruggedness in class-AB operation	3
8	Package outline	4
9	Abbreviations	6
10	Revision history	7
11	Legal information	8
11.1	Data sheet status	8
11.2	Definitions	8
11.3	Disclaimers	8
11.4	Trademarks	8
12	Contact information	8
13	Contents	9



Please be aware that important notices concerning this document and the product(s) described herein, have been included in section 'Legal information'.

© Koninklijke Philips Electronics N.V. 2006. All rights reserved.

For more information, please visit: <http://www.semiconductors.philips.com>.

For sales office addresses, email to: sales.addresses@www.semiconductors.philips.com.

Date of release: 19 April 2006

Document identifier: BLC6G10-200_6G10LS-200_1